

SILICON BRIDGE RECTIFIERS

Ready for use full-wave bridge rectifiers in a plastic encapsulation.

The bridges are intended for use in equipment supplied from a.c. with r.m.s. voltages up to 420 V and are capable of delivering output currents up to 12A. They are also suitable for use in hi-fi audio equipments and low-voltage industrial power supplies. They may be used in free air or on a heatsink.

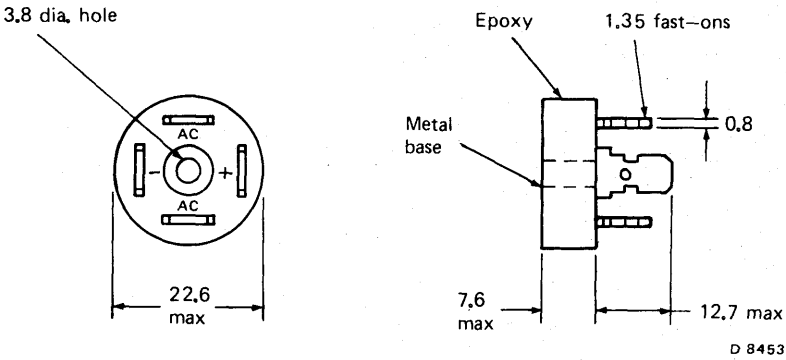
QUICK REFERENCE DATA

Input		BY260-200	400	600	
R.M.S. voltage	$V_I(RMS)$	max. 140	280	420	V
Repetitive peak voltage	$V_{IRM}$	max. 200	400	600	V
Non-repetitive peak current	$I_{ISM}$	max.	125		A
Peak inrush current	$I_{IIM}$	max.	250		A
Output					
Average current	$I_O(AV)$	max.	12		A

MECHANICAL DATA

Dimensions in mm

Fig. 1.



## RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134).

Input		BY260-200	400	600	
Non-repetitive peak voltage ( $t \leq 10$ ms)	$V_{ISM}$	max. 200	400	600	V
Repetitive peak voltage	$V_{IRM}$	max. 200	400	600	V
Crest working voltage	$V_{IWM}$	max. 200	400	600	V
R.M.S. voltage (sine-wave)	$V_{I(RMS)}$	max. 140	280	420	V
Non-repetitive peak current					
half-sinewave; $t = 20$ ms; with reapplied $V_{IWMmax}$					
$T_j = 25$ °C prior to surge	$I_{ISM}$	max.	125		A
$T_j = 150$ °C prior to surge	$I_{ISM}$	max.	100		A
Peak inrush current (see Fig. 5)	$I_{IIM}$	max.	250		A
Output					
Average current (averaged over any 20 ms period)					
heatsink operation up to $T_{mb} = 60$ °C (R-load)					
	$I_{O(AV)}$	max.	12		A
heatsink operation up to $T_{mb} = 60$ °C (C-load)					
	$I_{O(AV)}$	max.	7.5		A
Repetitive peak current	$I_{ORM}$	max.	20		A
Temperatures					
Storage temperature	$T_{stg}$		-55 to +150		°C
Junction temperature	$T_j$	max.	150		°C
THERMAL RESISTANCE					
From junction to mounting base	$R_{th j-mb}$	=	4.5		°C/W
CHARACTERISTICS					
Forward voltage (2 diodes in series)					
$I_F = 7$ A; $T_j = 25$ °C					
	$V_F$	<	2.0		V*
Reverse current (2 diodes in parallel)					
$V_R = V_{IWMmax}$ ; $T_j = 100$ °C					
	$I_R$	<	150		$\mu$ A

\*Measured under pulse conditions to avoid excessive dissipation.

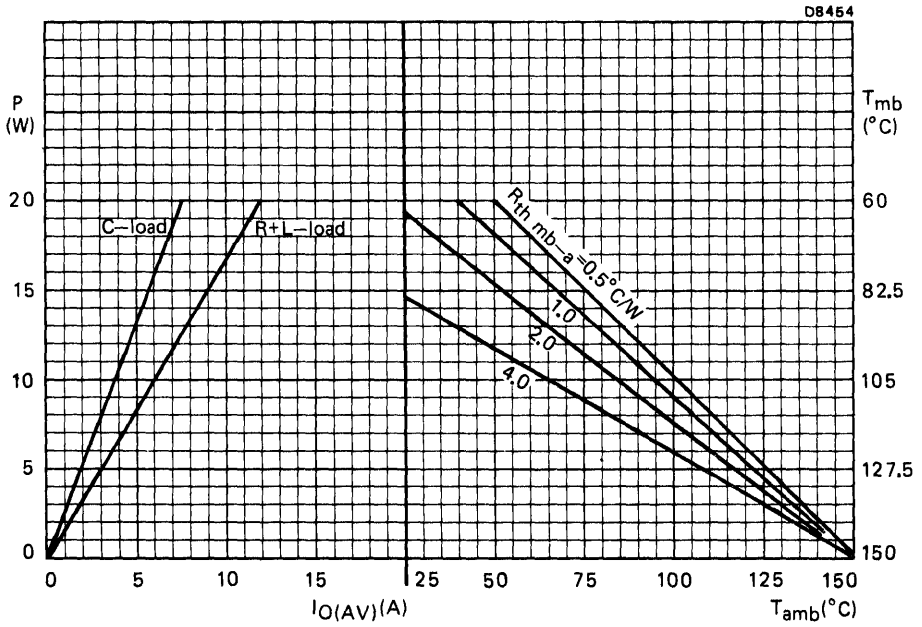


Fig.2 The right-hand part shows the interrelationship between the power (derived from the left-hand graph) and the maximum permissible temperatures.

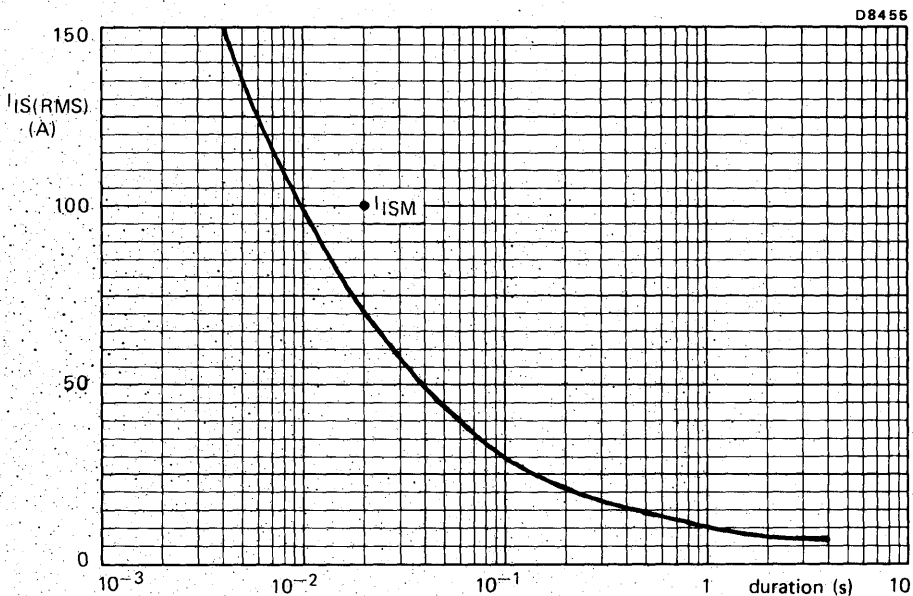


Fig.3 Maximum permissible non-repetitive r.m.s. input current based on sinusoidal currents ( $f = 50 \text{ Hz}$ );  $T_j = 150^\circ\text{C}$  prior to surge, with reapplied  $V_{IWMmax}$ .

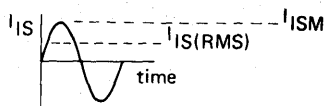
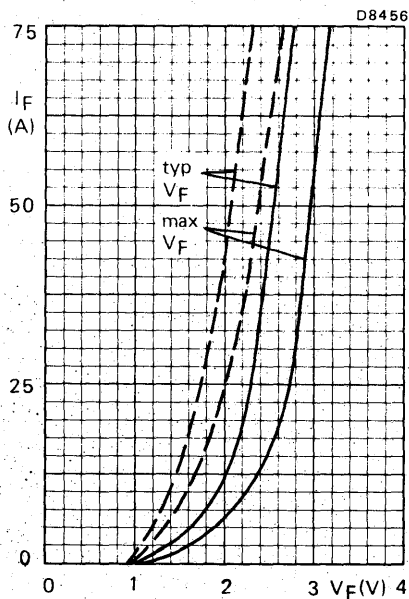
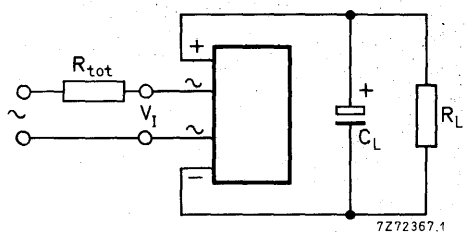
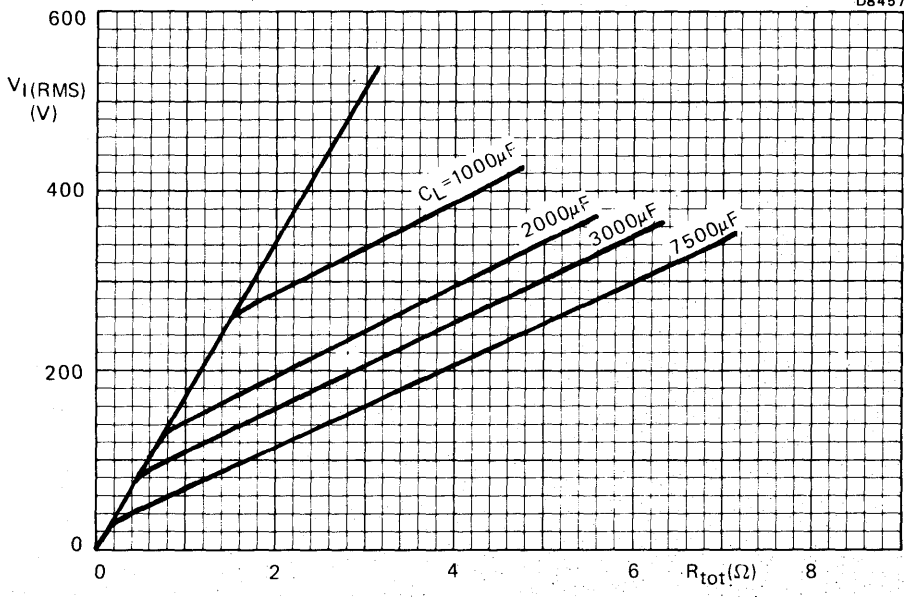


Fig.4 Two diodes in series;  
 —  $T_j = 25^\circ\text{C}$ ; - - -  $T_j = 150^\circ\text{C}$

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The graph takes the possibility of the following spreads into account:

- mains voltage +10%
- capacitance +50%
- resistance -10%

Fig.5 Minimum value of the total series resistance  $R_{tot}$  (including the transformer resistance) required to limit the peak inrush current.